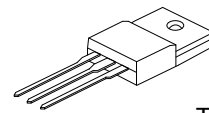


PNP EPITAXIAL SILICON TRANSISTOR

**POWER AMPLIFIER
APPLICATIONS DRIVER
STAGE AMPLIFIER
APPLICATIONS**

■ **FEATURES**

- * High Transition Frequency: $f_T=70\text{MHz}$ (Typ.)
- * Complementary to UTC **2SC4793**



TO-220F

■ **ABSOLUTE MAXIMUM RATING** ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Collector-Base Voltage			V _{CBO}	-150 ~ -230	V
Collector-Emitter Voltage			V _{CEO}	-150 ~ -230	V
Emitter-Base Voltage			V _{EBO}	-5	V
Collector Current			I _C	-1	A
Base Current			I _B	-0.1	A
Collector Power Dissipation	T _A =25°C	SOT-223	P _C	1	W
		TO-220		2	W
		TO-220F			
		TO-220F1			
		TO-220F2			
	T _C =25°C	SOT-223		15	W
		TO-220		20	W
		TO-220F			
TO-220F1					
TO-220F2					
Junction Temperature			T _J	+150	°C
Storage Temperature Range			T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -10\text{mA}$, $I_B = 0$	-150		-230	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -230\text{V}$, $I_E = 0$			-1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-1.0	μA
DC Current Gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -100\text{mA}$	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$			-1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5\text{V}$, $I_C = -500\text{mA}$			-1.0	V
Transition Frequency	f_T	$V_{CE} = -10\text{V}$, $I_C = -100\text{mA}$		70		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_C = 0$, $f = 1\text{MHz}$		30		pF

■ TYPICAL CHARACTERISTICS

